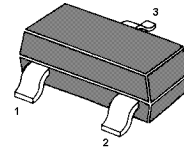


MMBT9014

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications

As complementary types the PNP transistor MMBT9015 is recommended.



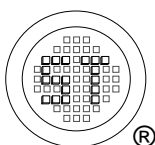
1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	45	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	MMBT9014B h_{FE}	110	220	-
	MMBT9014C h_{FE}	200	450	-
	MMBT9014D h_{FE}	420	800	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	50	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	50	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	45	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	0.25	V
Base Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	$V_{BE(sat)}$	-	1	V
Gain Bandwidth Product at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	f_T	100	-	MHz
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF



SEMTECH ELECTRONICS LTD.



ISO/TS 16949 : 2009 Certificate No. 160713000
ISO14001 : 2004 Certificate No. 7116
ISO 9001 : 2008 Certificate No. 90719410
BS-OHSAS 18001 : 2007 Certificate No. 7116
IECQ QC 080000 Certificate No. PRC-HSPM-1485-1

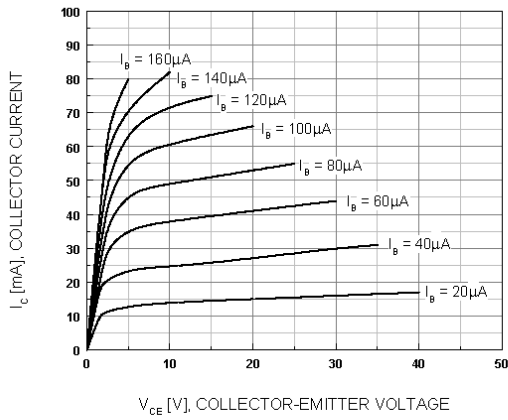


Figure 1. Static Characteristic

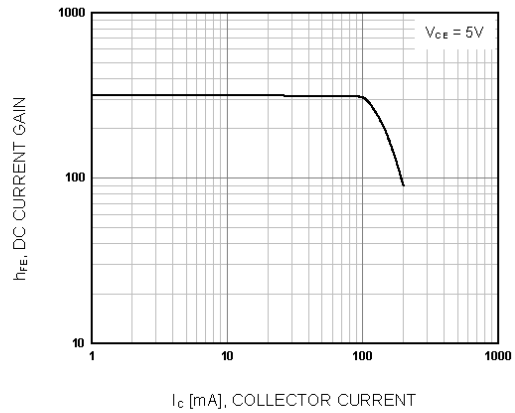


Figure 2. DC current Gain

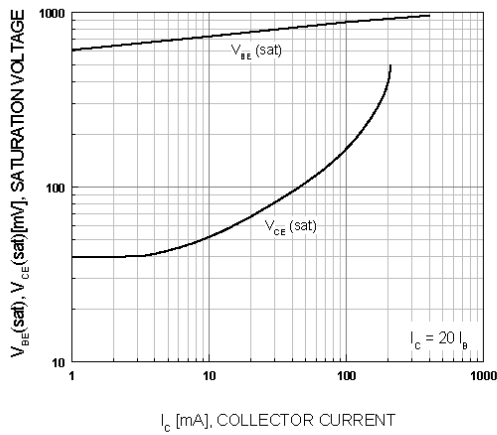


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

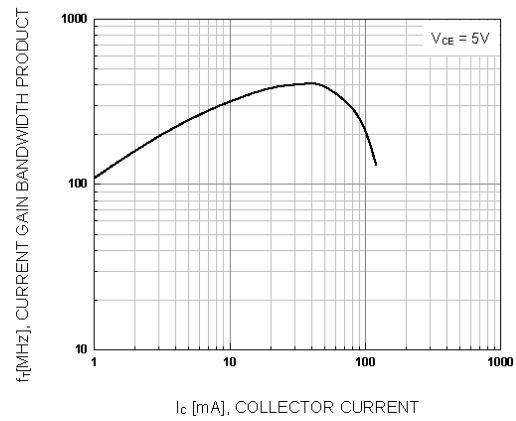
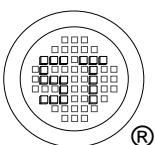


Figure 4. Current Gain Bandwidth Product

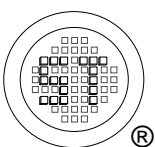
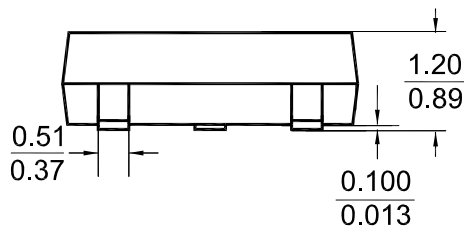
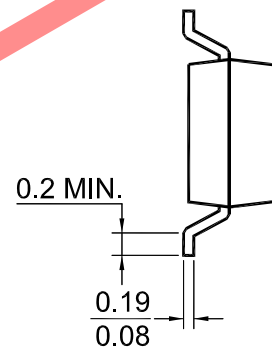
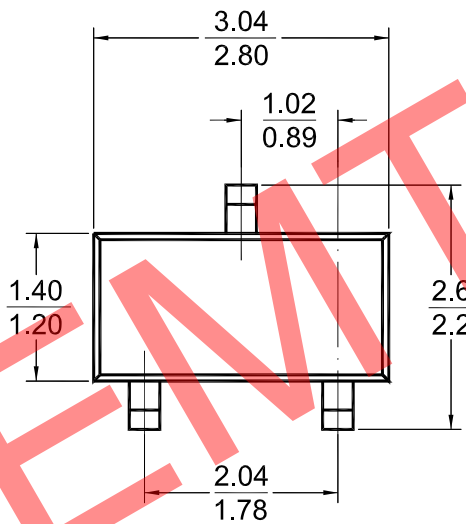
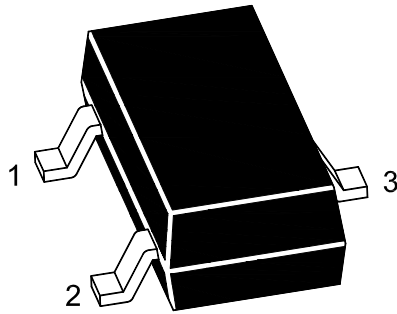


SEMTECH ELECTRONICS LTD.



TO-236 Package Outline

Package Outline Dimensions (Units: mm)



SEMTECH ELECTRONICS LTD.



Dated : 23/10/2010 Rev:01

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [Semtech manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)
[NTE195A](#) [NTE92](#) [C4460](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [2SC5488A-TL-H](#)
[2SD2150T100R](#) [SP000011176](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC2412KT146S](#) [2SD1816S-TL-E](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)
[MJE340](#) [US6T6TR](#) [NJL0281DG](#) [732314D](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#)
[NJL0302DG](#) [2N3583](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE13](#) [NTE26](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [STX83003-AP](#)